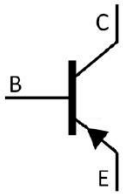


Rev. F Aug.-2018

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

600mA
 Collector currents to 600mA.

General purpose amplifier.



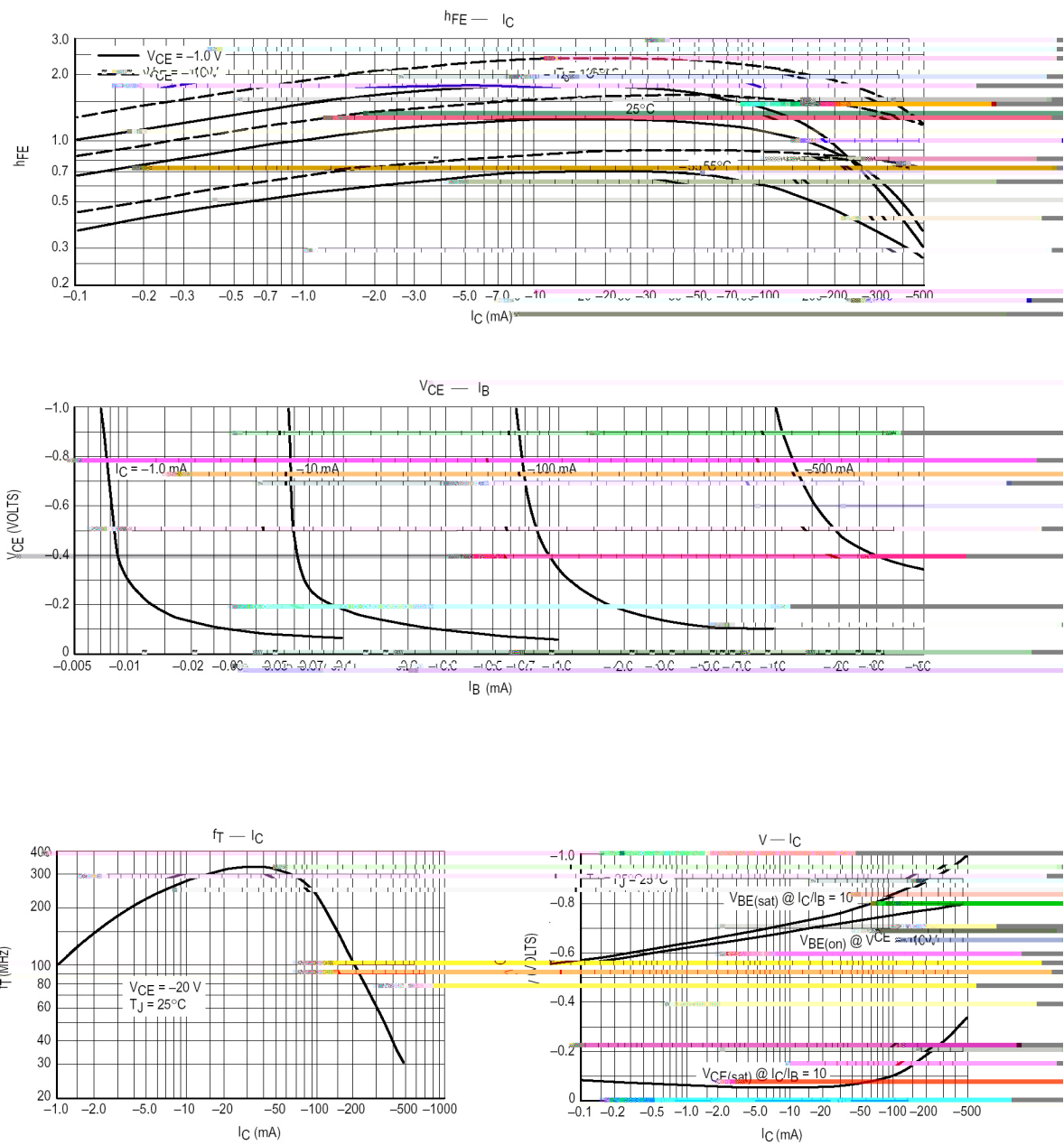
PIN 1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Range	100~300
Marking	H2B

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

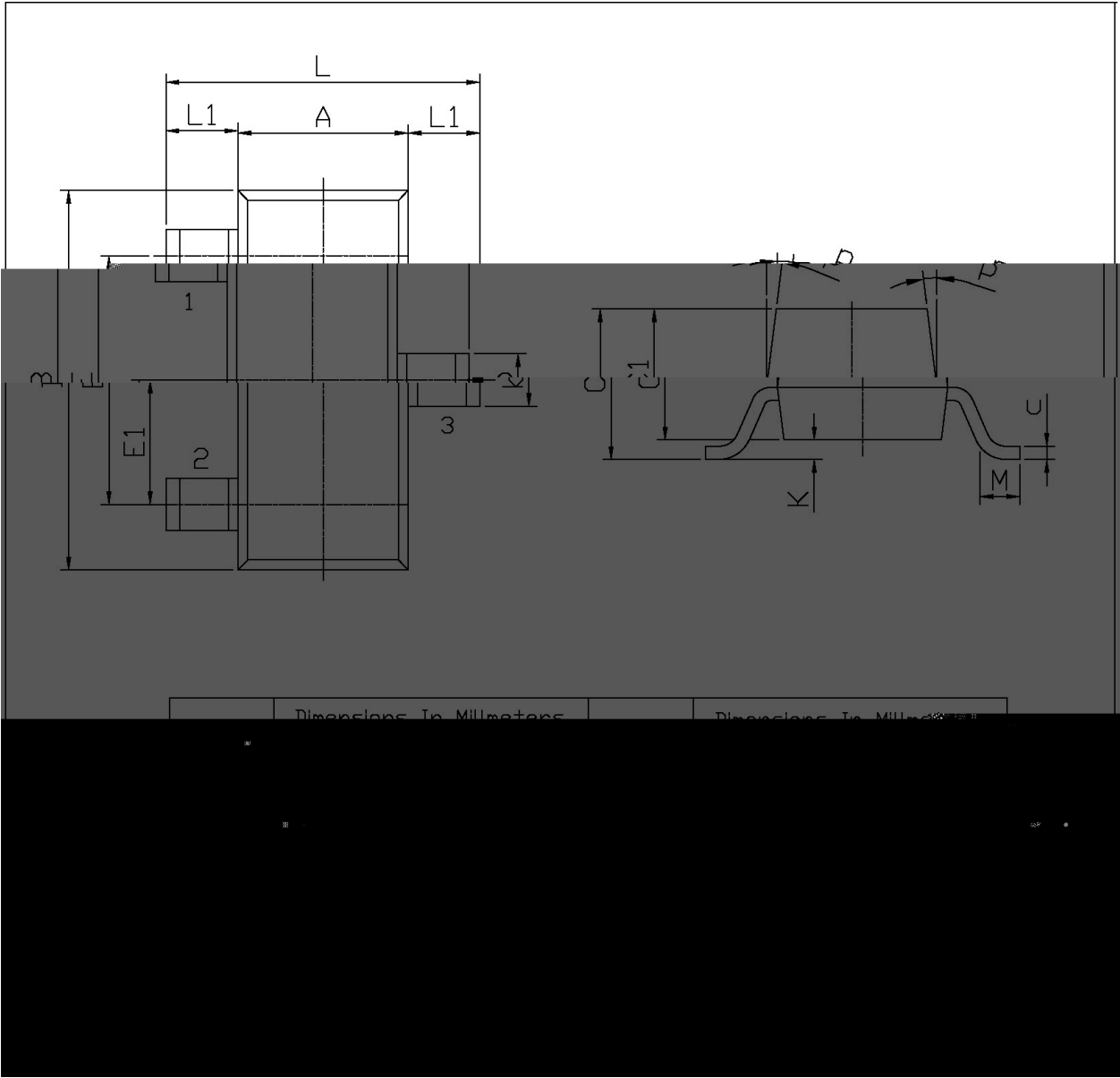
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\text{ A}$ $I_E = 0$	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10\text{ mA}$ $I_B = 0$	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\text{ A}$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -50\text{ V}$ $I_E = 0$			-0.02	A
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -10\text{ V}$ $I_C = -150\text{ mA}^*$	100		300	
	$h_{FE(2)}$	$V_{CE} = -10\text{ V}$ $I_C = -500\text{ mA}^*$	30			
	$h_{FE(3)}$	$V_{CE} = -10\text{ V}$ $I_C = -10\text{ mA}$	75			
	$h_{FE(4)}$	$V_{CE} = -10\text{ V}$ $I_C = -1.0\text{ mA}$	50			
	$h_{FE(5)}$	$V_{CE} = -10\text{ V}$ $I_C = -0.1\text{ mA}$	35			
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C = -150\text{ mA}$ $I_B = -15\text{ mA}$			-0.4	V
	$V_{CE(sat)(2)}$	$I_C = -500\text{ mA}$ $I_B = -50\text{ mA}$			-1.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C = -150\text{ mA}$ $I_B = -15\text{ mA}$			-1.3	V
	$V_{BE(sat)(2)}$	$I_C = -500\text{ mA}$ $I_B = -50\text{ mA}$			-2.6	V
Transition Frequency	f_T	$I_C = -50\text{ mA}$ $V_{CE} = -20\text{ V}$ $f = 100\text{ MHz}$	200			MHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{ V}$ $f = 1.0\text{ MHz}$			8.0	pF
Turn-On Time	t_{on}	$V_{CC} = -30\text{ V}$ $I_C = -150\text{ mA}$ $I_{B1} = -15\text{ mA}$			45	ns
Turn-Off Time	t_{off}	$V_{CC} = -6.0\text{ V}$ $I_C = -150\text{ mA}$ $I_{B1} = I_{B2} = -15\text{ mA}$			100	ns

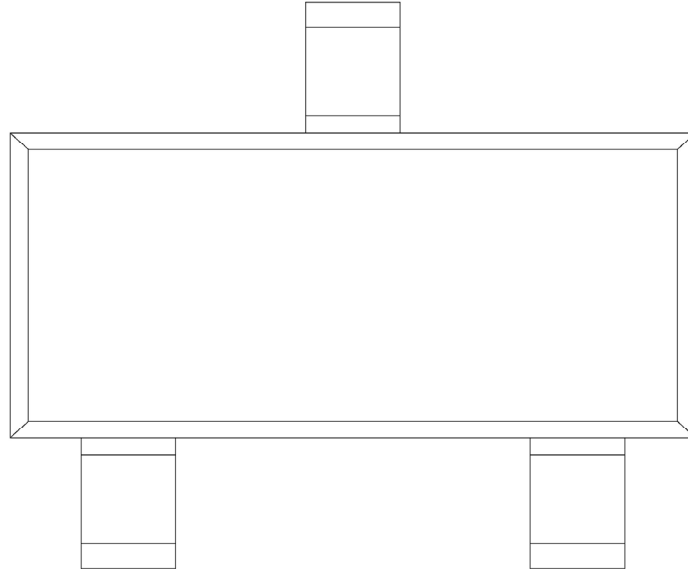
*Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$



SOT-23

单位; mm



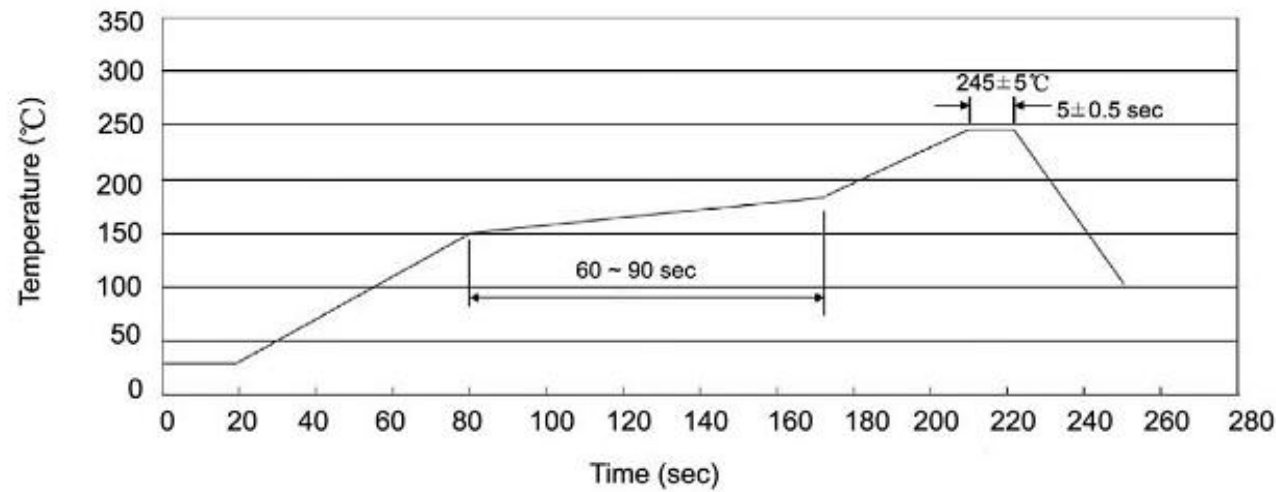


H

2B

Note:

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5℃

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						"		